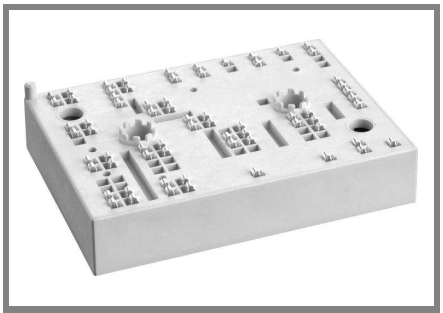
SKiiP 35NAB126V10



MiniSKiiP® 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter

SKiiP 35NAB126V10

Features

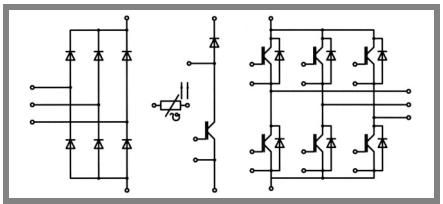
- Fast Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications*

- Inverter up to 28 kVA
- Typical motor power 15 kW

Remarks

- V_{CEsat} , V_F= chip level value



NAB

Absolute Maximum Ratings		T_s = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT - Inverter, Chopper			
V_{CES}		1200	V
I_C	T_s = 25 (70) °C	73 (55)	A
I_{CRM}		100	A
V_{GES}		± 20	V
T_j		- 40 ... + 150	°C
Diode - Inverter, Chopper			
I_F	T_s = 25 (70) °C	62 (46)	A
I_{FRM}		100	A
T_j		- 40 ... + 150	°C
Diode - Rectifier			
V_{RRM}		1600	V
I_F	T_s = 70 °C	67	A
I_{FSM}	t_p = 10 ms, sin 180 °, T_j = 25 °C	850	A
i^2t	t_p = 10 ms, sin 180 °, T_j = 25 °C	3600	A^2s
T_j		- 40 ... + 150	°C
Module			
I_{tRMS}	per power terminal (20 A / spring)	80	A
T_{stg}		- 40 ... + 125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics		T_s = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT - Inverter, Chopper					
V_{CEsat}	I_{Cnom} = 50 A, T_j = 25 (125) °C		1,7 (2)	2,1 (2,4)	V
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2 mA	5	5,8	6,5	V
$V_{CE(TO)}$	T_j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r_T	T_j = 25 (125) °C		14 (22)	18 (26)	mΩ
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		3,7		nF
C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,8		nF
C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,7		nF
$R_{th(j-s)}$	per IGBT		0,55		K/W
$t_{d(on)}$	under following conditions		85		ns
t_r	V_{CC} = 600 V, V_{GE} = ± 15 V		30		ns
$t_{d(off)}$	I_{Cnom} = 50 A, T_j = 125°C		430		ns
t_f	R_{Gon} = R_{Goff} = 12 Ω		90		ns
E_{on}	inductive load		6,5		mJ
E_{off}			6,1		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	I_{Fnom} = 50 A, T_j = 25 (125) °C		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	T_j = 25 (125) °C		1 (0,8)	1,1 (0,9)	V
r_T	T_j = 25 (125) °C		12 (16)	14 (18)	mΩ
$R_{th(j-s)}$	per diode		1		K/W
I_{RRM}	under following conditions		71		A
Q_{rr}	I_{Fnom} = 50 A, V_R = 600 V		11,5		µC
E_{rr}	V_{GE} = 0 V, T_j = 125 °C		4,7		mJ
	di_F/dt = 1900 A/µs				
Diode - Rectifier					
V_F	I_{Fnom} = 40 A, T_j = 25 °C		1,1		V
$V_{(TO)}$	T_j = 125 °C		0,8		V
r_T	T_j = 125 °C		9		mΩ
$R_{th(j-s)}$	per diode		0,85		K/W
Temperature Sensor					
R_{ts}	3 %, T_r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			95		g
M_s	Mounting torque	2		2,5	Nm

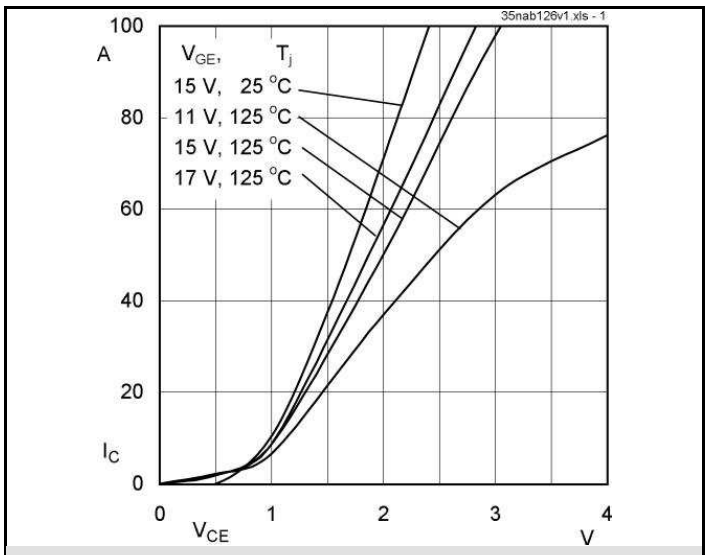


Fig. 1 Typ. output characteristic

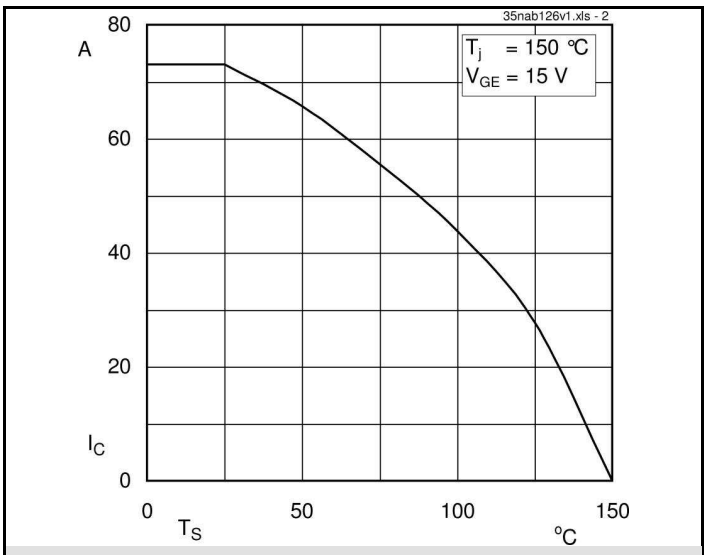


Fig. 2 Typ. rated current vs. temperature

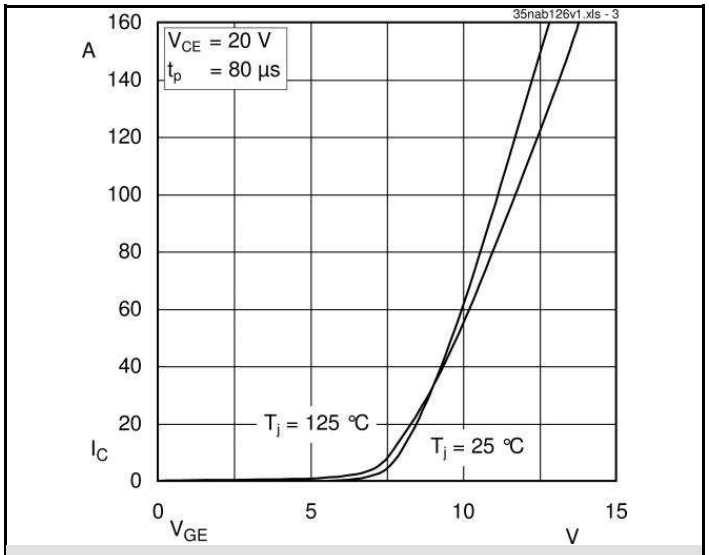


Fig. 3 Typ. transfer characteristic

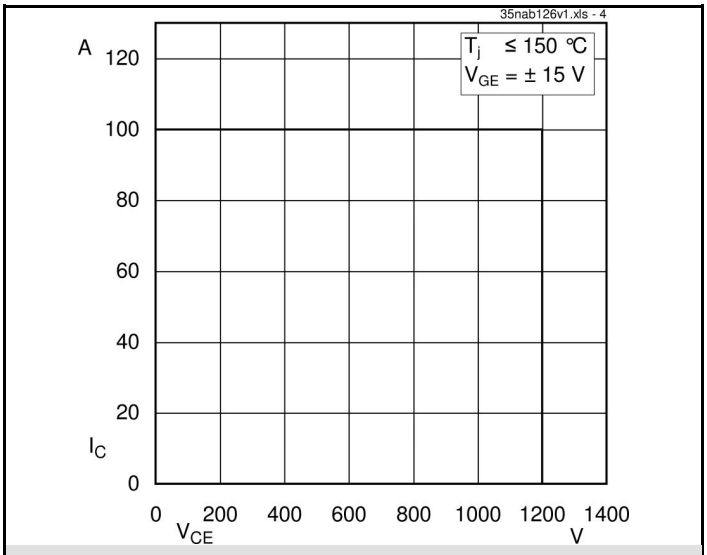


Fig. 4 Reverse bias safe operating area

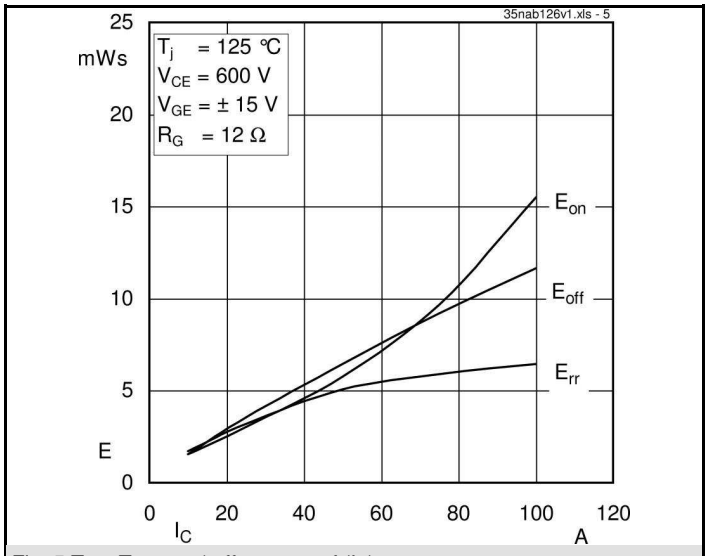


Fig. 5 Typ. Turn-on /-off energy = f (I_C)

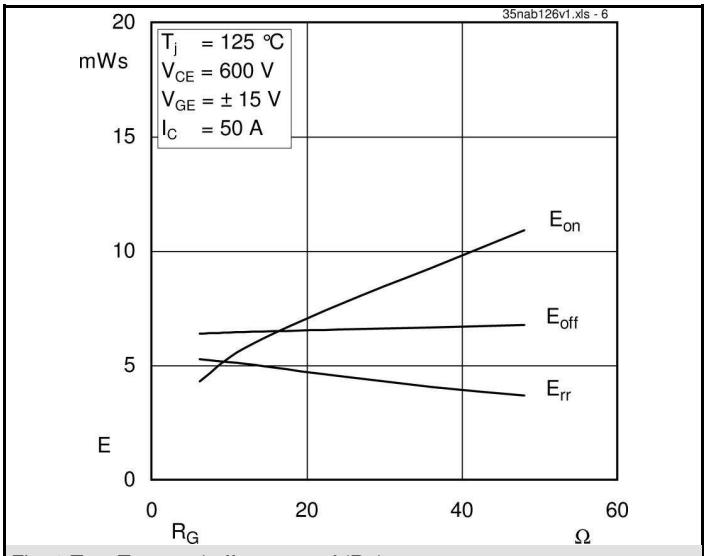


Fig. 6 Typ. Turn-on /-off energy = f (R_G)

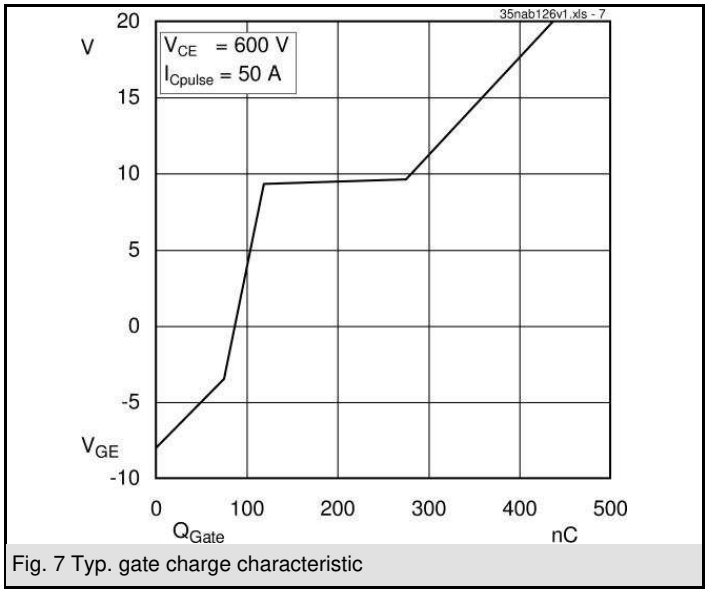


Fig. 7 Typ. gate charge characteristic

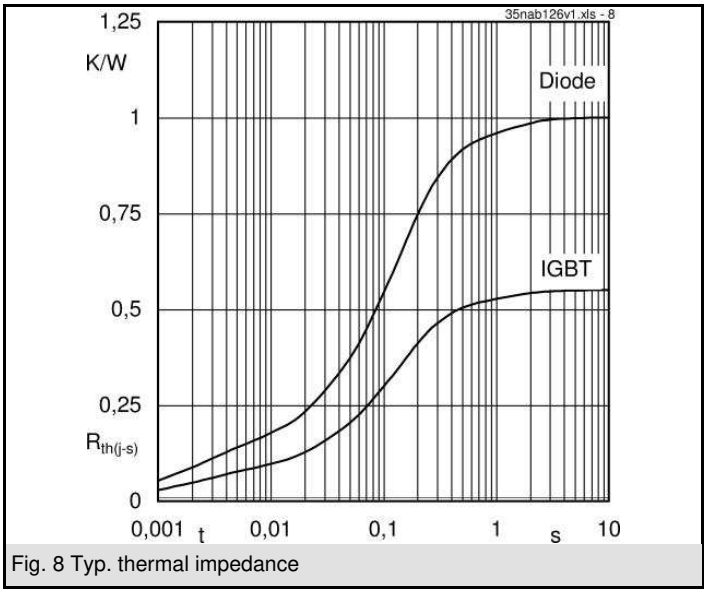


Fig. 8 Typ. thermal impedance

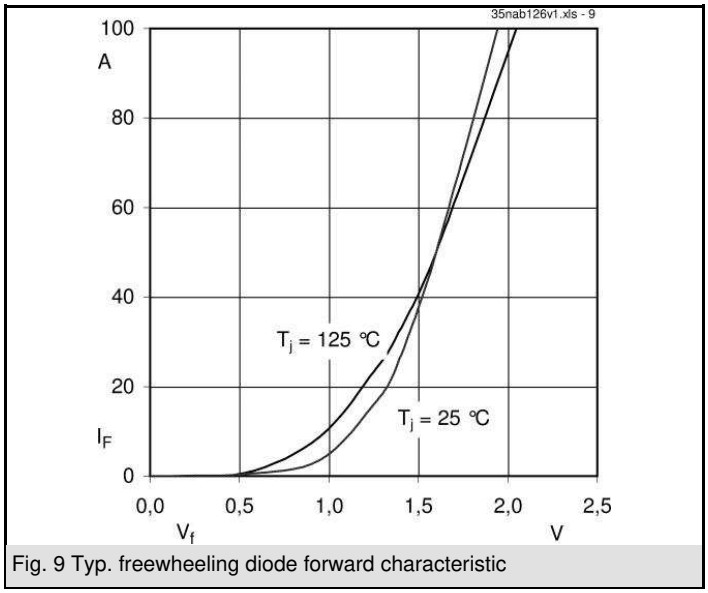


Fig. 9 Typ. freewheeling diode forward characteristic

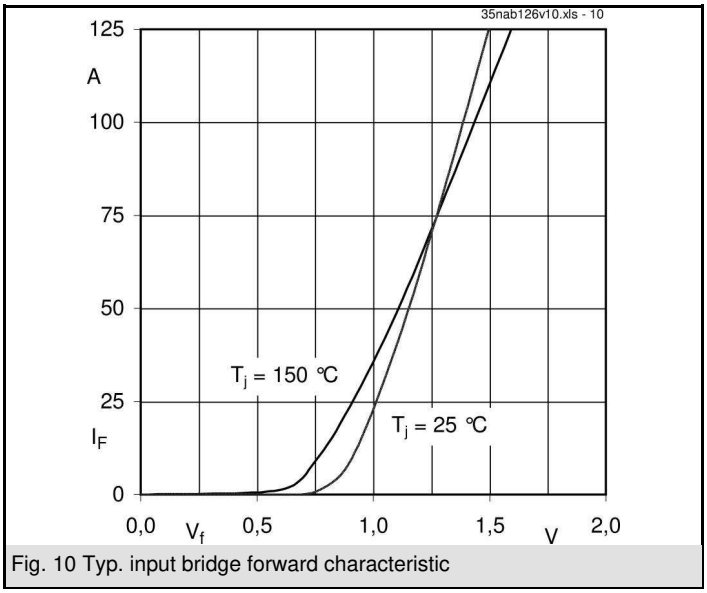
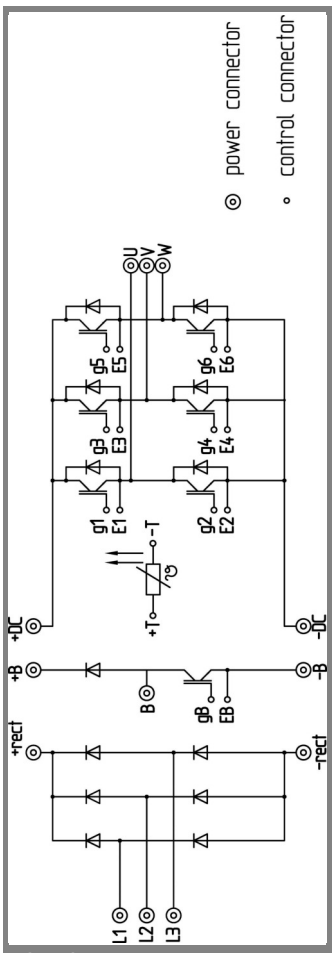
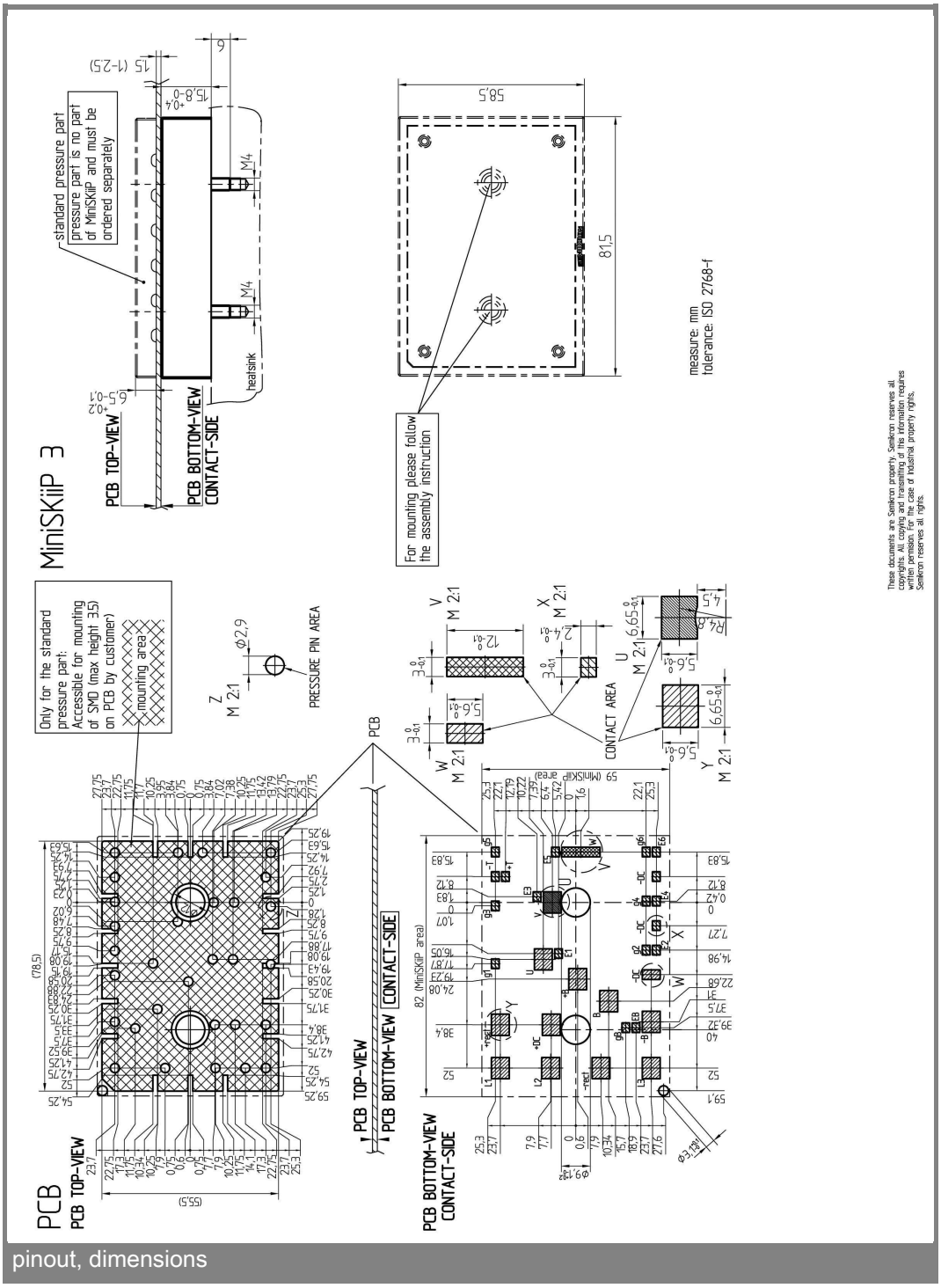


Fig. 10 Typ. input bridge forward characteristic



circuit



pinout, dimensions

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.